

## N-Channel Power MOSFET

600V, 0.6A, 5Ω

### FEATURES

- Robust high voltage termination
- Avalanche energy specified
- Diode is characterized for use in bridge circuits
- Source to Drain diode recovery time comparable to a discrete fast recovery diode.

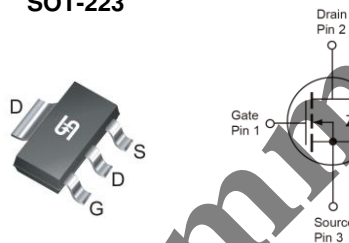
KEY PERFORMANCE PARAMETERS		
PARAMETER	VALUE	UNIT
$V_{DS}$	600	V
$R_{DS(on)}$ (max)	5	Ω
$Q_g$	13	nC

### APPLICATION

- Power Supply
- Lighting
- Charger



SOT-223



**Notes:** MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	600	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	V
Continuous Drain Current (Note 1)	$I_D$	$T_C = 25^\circ\text{C}$	0.6
		$T_C = 100^\circ\text{C}$	0.36
Pulsed Drain Current (Note 2)	$I_{DM}$	1.5	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	$P_{DTOT}$	2.5	W
Single Pulsed Avalanche Energy (Note 3)	$E_{AS}$	62	mJ
Single Pulsed Avalanche Current (Note 3)	$I_{AS}$	2.5	A
Operating Junction Temperature	$T_J$	150	$^\circ\text{C}$
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	- 55 to +150	$^\circ\text{C}$

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	15	$^\circ\text{C/W}$
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	55.8	$^\circ\text{C/W}$

**Notes:**  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\theta JA}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.  $R_{\theta JA}$  shown below for single device operation on FR-4 PCB with minimum recommended footprint in still air

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
<b>Static</b> (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	$BV_{DSS}$	600	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(TH)}$	2	--	4	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	$I_{GSS}$	--	--	$\pm 100$	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	$I_{DSS}$	--	--	1	$\mu A$
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 0.6A$	$R_{DS(ON)}$	--	3.6	5	$\Omega$
Forward Transconductance	$V_{DS} = 10V, I_D = 0.2A$	$g_{fs}$	--	0.8	--	S
<b>Dynamic</b> (Note 5)						
Total Gate Charge	$V_{DS} = 400V, I_D = 0.6A,$ $V_{GS} = 10V$	$Q_g$	--	13	--	nC
Gate-Source Charge		$Q_{gs}$	--	2	--	
Gate-Drain Charge		$Q_{gd}$	--	6	--	
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0MHz$	$C_{iss}$	--	435	--	pF
Output Capacitance		$C_{oss}$	--	56	--	
Reverse Transfer Capacitance		$C_{rss}$	--	9.2	--	
<b>Switching</b> (Note 6)						
Turn-On Delay Time	$V_{GS} = 10V, I_D = 0.6A,$ $V_{DD} = 300V, R_G = 18\Omega,$	$t_{d(on)}$	--	12	--	ns
Turn-On Rise Time		$t_r$	--	21	--	
Turn-Off Delay Time		$t_{d(off)}$	--	30	--	
Turn-Off Fall Time		$t_f$	--	24	--	
<b>Source-Drain Diode</b> (Note 4)						
Forward On Voltage	$I_S = 0.6A, V_{GS} = 0V$	$V_{SD}$	--	0.85	1.15	V

**Notes:**

1. Current limited by package
2. Pulse width limited by the maximum junction temperature
3.  $L = 20mH, I_{AS} = 2.5A, V_{DD} = 50V, R_G = 25\Omega,$  Starting  $T_J = 25^\circ\text{C}$
4. Pulse test:  $PW \leq 300\mu s,$  duty cycle  $\leq 2\%$
5. For DESIGN AID ONLY, not subject to production testing.
6. Switching time is essentially independent of operating temperature.

**ORDERING INFORMATION**

<b>PART NO.</b>	<b>PACKAGE</b>	<b>PACKING</b>
TSM2N60SCW RPG	SOT-223	2,500pcs / 13" Reel

**Note:**

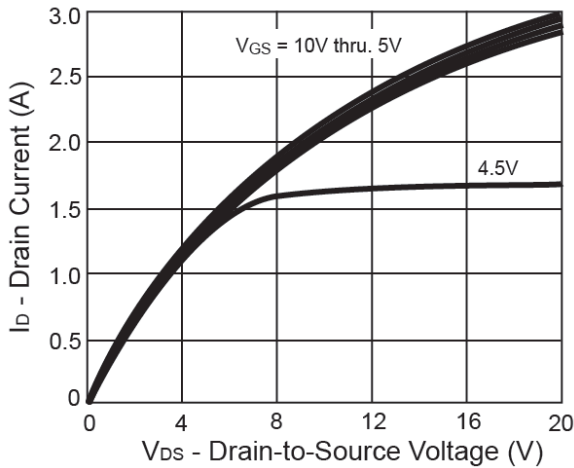
1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
2. Halogen-free according to IEC 61249-2-21 definition

**Not Recommended**

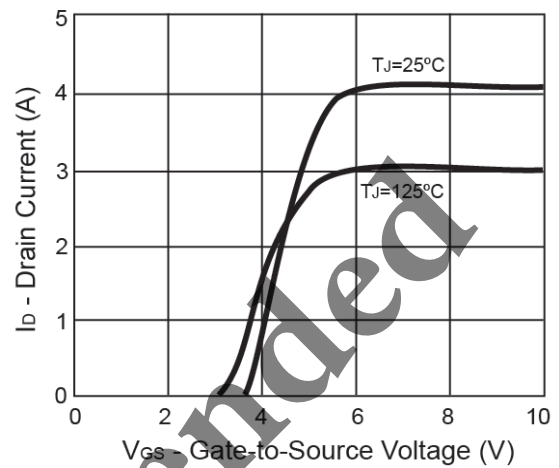
**CHARACTERISTICS CURVES**

( $T_C = 25^\circ\text{C}$  unless otherwise noted)

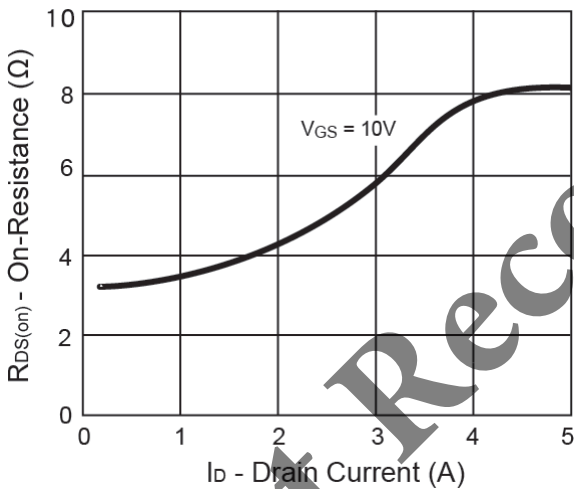
**Output Characteristics**



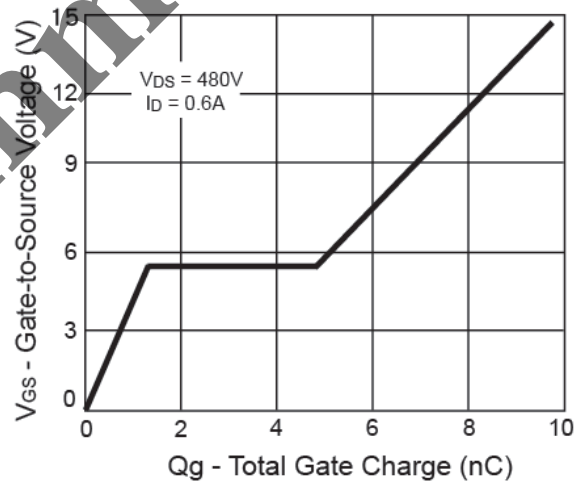
**Transfer Characteristics**



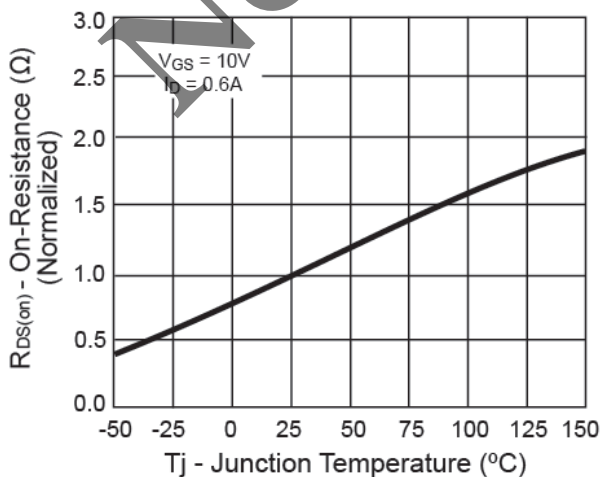
**On-Resistance vs. Drain Current**



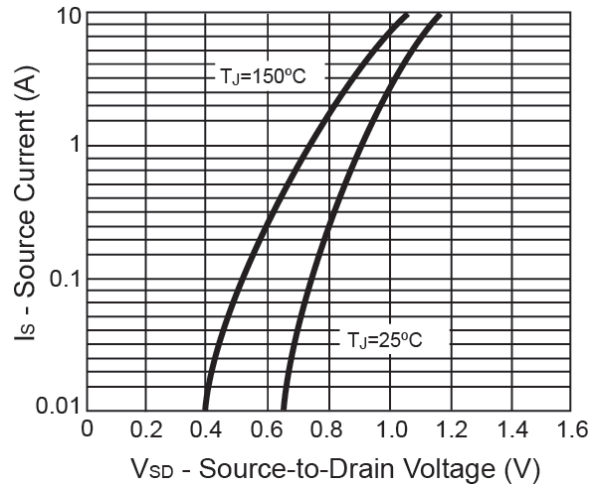
**Gate Charge**



**On-Resistance vs. Junction Temperature**



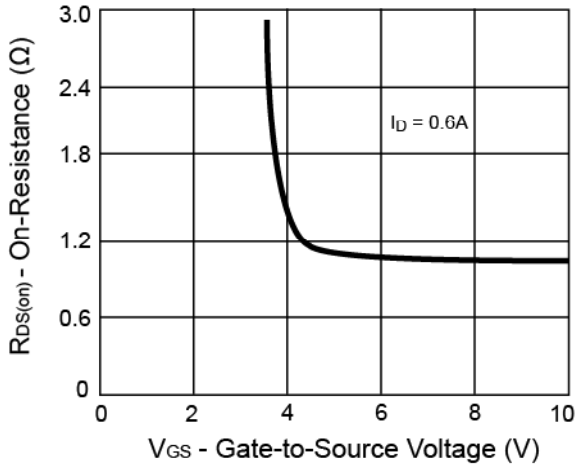
**Source-Drain Diode Forward Voltage**



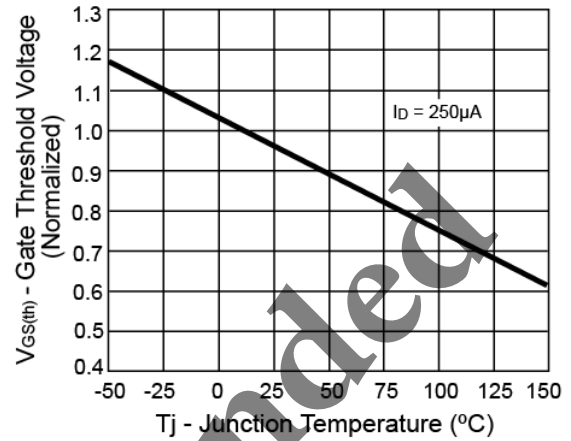
**CHARACTERISTICS CURVES**

(Tc = 25°C unless otherwise noted)

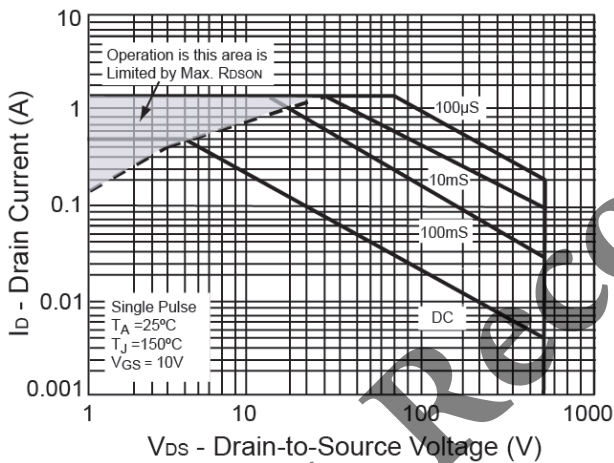
**On-Resistance vs. Gate-Source Voltage**



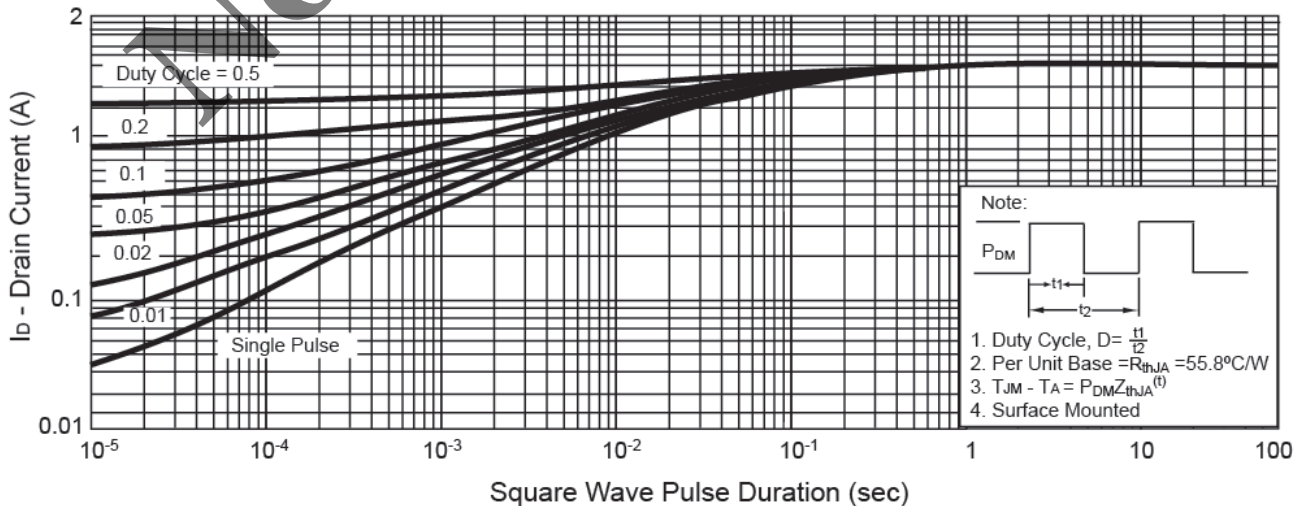
**Threshold Voltage**



**Maximum Safe Operating Area**

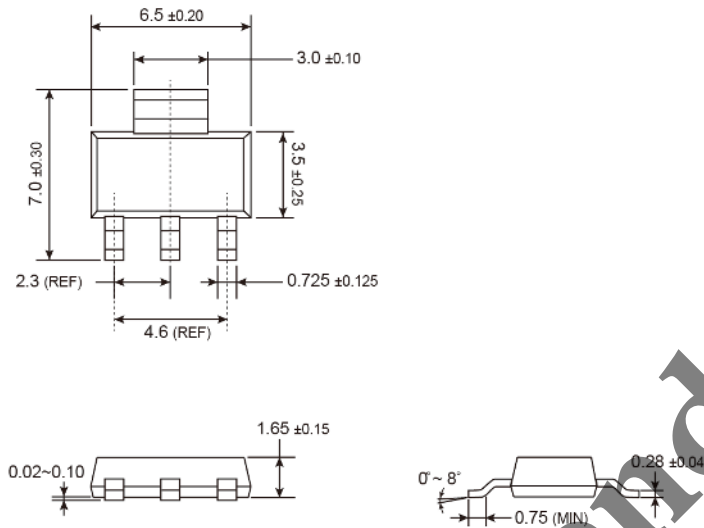


**Normalized Thermal Transient Impedance, Junction-to-Ambient**

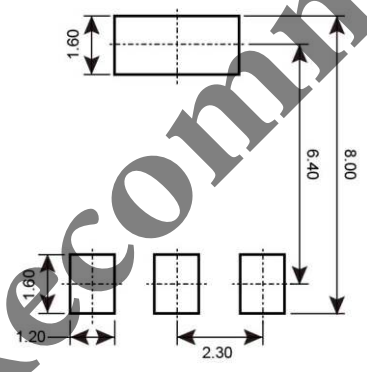


**PACKAGE OUTLINE DIMENSIONS** (Unit: Millimeters)

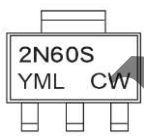
**SOT-223**



**SUGGESTED PAD LAYOUT**



**MARKING DIAGRAM**



- Y** = Year Code
- M** = Month Code for Halogen Free Product
- O** =Jan    **P** =Feb    **Q** =Mar    **R** =Apr
- S** =May    **T** =Jun    **U** =Jul    **V** =Aug
- W** =Sep    **X** =Oct    **Y** =Nov    **Z** =Dec
- L** = Lot Code (1~9, A~Z)

**Not Recommended**

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